

Yong Seung Kim

List of Publications by Year in descending order

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Version: 2024-02-01

19
papers

1,688
citations

567281

15
h-index

888059

17
g-index

19
all docs

19
docs citations

19
times ranked

3243
citing authors

#	ARTICLE	IF	CITATIONS
1	Universality of periodicity as revealed from interlayer-mediated cracks. Scientific Reports, 2017, 7, 43400.	3.3	8
2	Terahertz funneling-induced quantum tunneling at angstrom scale. , 2016, , .		1
3	Tunnelling current-voltage characteristics of Angstrom gaps measured with terahertz time-domain spectroscopy. Scientific Reports, 2016, 6, 29103.	3.3	18
4	Colossal Terahertz Nonlinearity in Angstrom- and Nanometer-Sized Gaps. ACS Photonics, 2016, 3, 1440-1445.	6.6	18
5	Terahertz Quantum Plasmonics at Angstrom Scale. , 2016, , .		0
6	Electromagnetic Saturation of Angstrom-Sized Quantum Barriers at Terahertz Frequencies. Physical Review Letters, 2015, 115, 125501.	7.8	60
7	Polarized Raman spectroscopy with differing angles of laser incidence on single-layer graphene. Nanoscale Research Letters, 2015, 10, 45.	5.7	20
8	Bright visible light emission from graphene. Nature Nanotechnology, 2015, 10, 676-681.	31.5	284
9	Direct Integration of Polycrystalline Graphene into Light Emitting Diodes by Plasma-Assisted Metal-Catalyst-Free Synthesis. ACS Nano, 2014, 8, 2230-2236.	14.6	55
10	Graphene film growth on sputtered thin Cu-Ni alloy film by inductively coupled plasma chemical vapor deposition. RSC Advances, 2014, 4, 63349-63353.	3.6	6
11	Direct growth of patterned graphene on SiO ₂ substrates without the use of catalysts or lithography. Nanoscale, 2014, 6, 10100-10105.	5.6	66
12	Spin valve effect of NiFe/graphene/NiFe junctions. Nano Research, 2013, 6, 373-380.	10.4	79
13	Ordered growth of topological insulator Bi ₂ Se ₃ thin films on dielectric amorphous SiO ₂ by MBE. Nanoscale, 2013, 5, 10618.	5.6	64
14	Methane as an effective hydrogen source for single-layer graphene synthesis on Cu foil by plasma enhanced chemical vapor deposition. Nanoscale, 2013, 5, 1221.	5.6	104
15	Focused-Laser-Enabled p-n Junctions in Graphene Field-Effect Transistors. ACS Nano, 2013, 7, 5850-5857.	14.6	76
16	Thickness-Independent Transport Channels in Topological Insulator Bi_2Se_3 Films. Physical Review Letters, 2012, 109, 116804.	7.8	306
17	Surface versus bulk state in topological insulator Bi ₂ Se ₃ under environmental disorder. Applied Physics Letters, 2011, 99, .	3.3	73
18	Epitaxial growth of topological insulator Bi ₂ Se ₃ film on Si(111) with atomically sharp interface. Thin Solid Films, 2011, 520, 224-229.	1.8	180

#	ARTICLE	IF	CITATIONS
19	<p> Time-reversal symmetry-dependent bulk properties and weak antilocalization effect in topological insulator $Bi_{1-x}Sb_x$ $Se_{1-x}Te_x$ $Sb_{1-x}Te_x$. Physical Review B, 2011, 84, . </p>	3.2	270